# A METHOD TO FABRICATE A STRAINED Si CMOS STRUCTURE USING SELECTIVE EPITAXIAL DEPOSITION OF Si AFTER DEVICE ISOLATION FORMATION

## ABSTRACT OF THE DISCLOSURE

A strained Si CMOS structure is formed by steps which include forming a relaxed SiGe layer (12) on a surface of a substrate (10); forming isolation regions (14) and well implant regions (16) in said relaxed SiGe layer (12); and forming a strained Si layer (18) on said relaxed SiGe layer (12). These processing steps may be used in conjunction with conventional gate processing steps in forming a strained MOSFET structure.

**Fig. 3**

This Sheet Has Been Replaced

